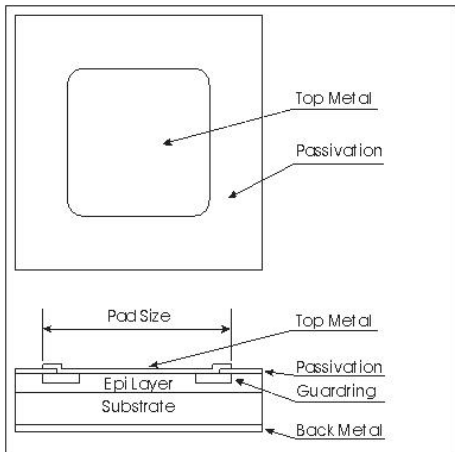


# TRENCH SCHOTTKY DIODE SPECIFICATION

PART NO.	Document ID	DATE	REV.
Y59A05G045	CS-1Y05902	2014.5.10	B



Item	Characteristics	
Chip Size	1504*1504 um	59.2*59.2 mil
Pad Size	1436*1436 um	56.5*56.5 mil
Chip Thickness	246-271 um	9.7-10.7 mil
Scribe Line Width	30 um	1.18 mil
Wafer Size	6 inch	150.00 mm
Passivation	SiO <sub>2</sub>	
Top Metallization	Ag	
Back Metallization	Ag	

Item	Symbol	Max. Rating	Unit
Peak reverse voltage	$V_{RM}$	45	V
DC reverse voltage	$V_R$		
Mean rectifying current	$I_o$	5	A
Peak forward surge current	$I_{FSM}$	120	A
Junction temperature	$T_j$	-50~+125	°C
Storage temperature	$T_{stg}$	-50~+150	°C

### Electrical Characteristics (Ta = 25 °C)

Item	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Breakdown Voltage	VB	46			V	IR=500uA
Maximum Instantaneous Reverse Current	IR			200	uA	VR=46V
Maximum Instantaneous Forward Voltage	VF			470 530	mV	IF=5A IF=10A

表單編號 3-PE-001-01-B